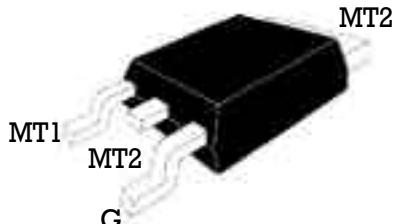


SURFACE MOUNT TRIAC

DPAK (Plastic) 	On-State Current 4 Amp	Gate Trigger Current < 5 mA to < 35 mA
	Off-State Voltage 200 V ÷ 600 V	
<p>This series of TRIACs uses a high performance PNPN technology.</p> <p>These devices are intended for AC control applications using surface mount technology.</p> <p>The high commutation performances combined with high sensitivity, make them perfect in all applications like solid state relays, home appliances, power tools, small motor drives...</p>		

Absolute Maximum Ratings, according to IEC publication No. 134

SYMBOL	PARAMETER	CONDITIONS	Min.	Max.	Unit
$I_{T(RMS)}$	RMS On-state Current	All Conduction Angle, $T_c = 110^\circ C$	4		A
I_{TSM}	Non-repetitive On-State Current	Half Cycle, 60 Hz	31		A
I_{TSM}	Non-repetitive On-State Current	Half Cycle, 50 Hz	30		A
I^{2t}	Fusing Current	$t_p = 10 \text{ ms}$, Half Cycle	5.1		A^2s
I_{GM}	Peak Gate Current	20 μs max.		4	A
P_{GM}	Peak Gate Dissipation	20 μs max.		3	W
$P_{G(AV)}$	Gate Dissipation	20 ms max.		1	W
di/dt	Critical rate of rise of on-state current	$I_G = 2 \times I_{GT} \text{ Tr } 200 \text{ ns}, F = 120 \text{ Hz}$ $T_j = 125^\circ C$	50		$\text{A}/\mu\text{s}$
T_j	Operating Temperature			+125	$^\circ C$
T_{stg}	Storage Temperature		-40	+150	$^\circ C$
T_L	Lead Temperature for Soldering	4.5 mm from case, 10s max.	-40	260	$^\circ C$

SYMBOL	PARAMETER	VOLTAGE			Unit
		B	D	M	
V_{DRM}	Repetitive Peak Off State Voltage	200	400	600	V
V_{RRM}					

SURFACE MOUNT TRIAC

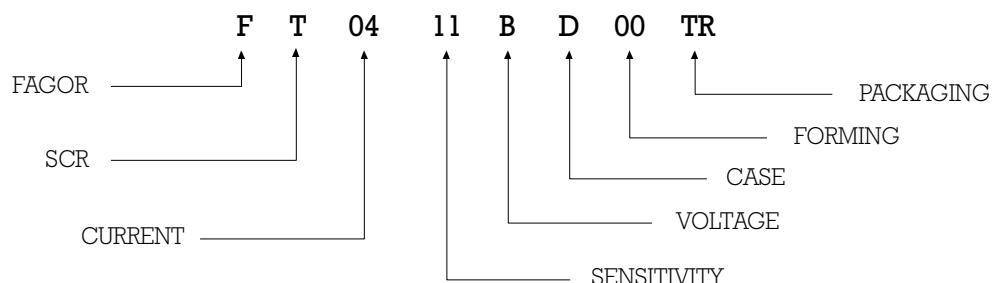
Electrical Characteristics

SYMBOL	PARAMETER	CONDITIONS	Quadrant		SENSITIVITY				Unit
					07	08	11	14	
$I_{GT}^{(1)}$	Gate Trigger Current	$V_D = 12 V_{DC}$, $R_L = 30 \Omega$ $T_j = 25^\circ C$	Q1-Q3 Q4	MAX	5	10	25	35	mA
					7				mA
I_{DRM}/I_{RRM}	Off-State Leakage Current	$V_R = V_{DRM}$, $T_j = 125^\circ C$ $V_R = V_{RRM}$, $T_j = 25^\circ C$		MAX			1		mA
							5		μA
$V_{to}^{(2)}$	Threshold Voltage	$T_j = 125^\circ C$		MAX			0.9		V
$R_d^{(2)}$	Dynamic Resistance	$T_j = 125^\circ C$		MAX			120		m
$V_{TM}^{(2)}$	On-state Voltage	$I_T = 5.5 \text{ Amp}$, $t_p = 380 \mu s$, $T_j = 25^\circ C$		MAX			1.6		V
V_{GT}	Gate Trigger Voltage	$V_D = 12 V_{DC}$, $R_L = 30 \Omega$, $T_j = 25^\circ C$	Q1-Q3	MAX			1.3		V
V_{GD}	Gate Non Trigger Voltage	$V_D = V_{DRM}$, $R_L = 3.3K$, $T_j = 125^\circ C$	Q1-Q3	MIN			0.2		V
$I_H^{(2)}$	Holding Current	$I_T = 100 \text{ mA}$, Gate open, $T_j = 25^\circ C$		MAX	10	15	25	35	mA
I_L	Latching Current	$I_G = 1.2 I_{GT}$, $T_j = 25^\circ C$	Q1,Q3 Q2	MAX	10	20	25	50	mA
					15	30	50	60	
$dv/dt^{(2)}$	Critical Rate of Voltage Rise	$V_D = 0.67 \times V_{DRM}$, Gate open $T_j = 125^\circ C$		MIN	20	100	200	400	V/ μs
$(dI/dt)c^{(2)}$	Critical Rate of Current Rise	$(dI/dt)c = 0.1 \text{ V}/\mu s$, $T_j = 125^\circ C$		MIN	1.8	2.7	4.4	-	A/ms
		$(dI/dt)c = 10 \text{ V}/\mu s$, $T_j = 125^\circ C$		MIN	0.9	2.0	2.7	-	
		without snubber, $T_j = 125^\circ C$		MIN	-	-	-	2.5	
t_{gd}	Gate Controlled Delay Time	$I_G = 2xI_{GT}$, $V_D = V_{DRM}$ $dI_G/dt = 3 \text{ A}/\mu s$, $I_{TM} = 5.5 \text{ A}$	Q1-Q3	TYP			2		μs
$R_{th(j-c)}$	Thermal Resistance Junction-Case						2.6		$^\circ C/W$
$R_{th(j-a)}$	Thermal Resistance Junction-Ambient						70		$^\circ C/W$

(1) Minimum I_{GT} is guaranteed at 5% of I_{GT} max.

(2) For either polarity of electrode MT2 voltage with reference to electrode MT1.

PART NUMBER INFORMATION



SURFACE MOUNT TRIAC

Fig. 1: Maximum power dissipation versus RMS on-state current

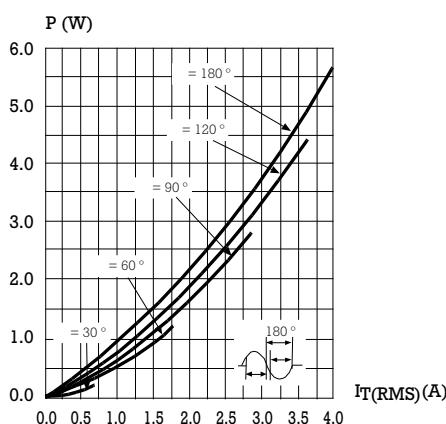


Fig. 3: RMS on-state current versus ambient temperature

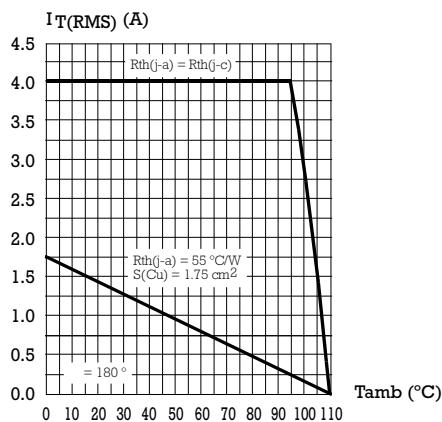


Fig. 5: Relative variation of gate trigger current and holding current versus junction temperature (typical values).

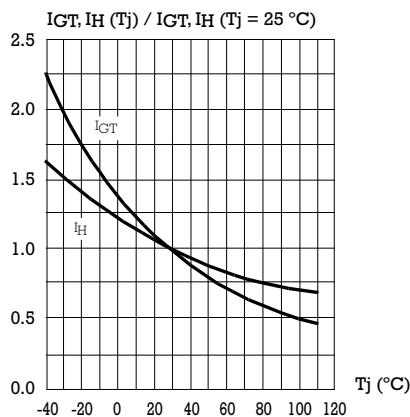


Fig. 2: Correlation between maximum power dissipation and maximum allowable temperatures (Tamb and Tcase) for different thermal resistances heatsink + contact.

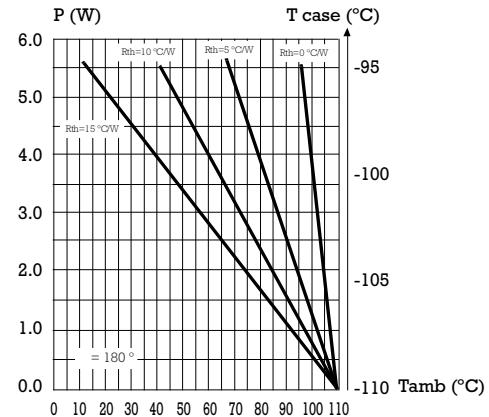


Fig. 4: Relative variation of thermal impedance junction to case versus pulse duration.

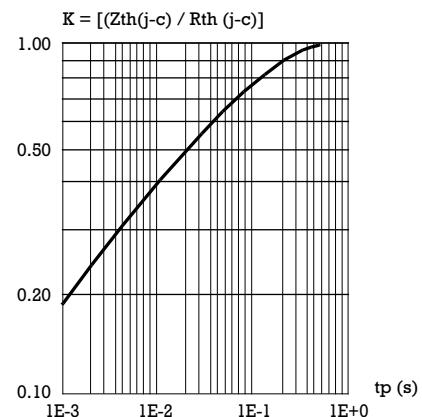
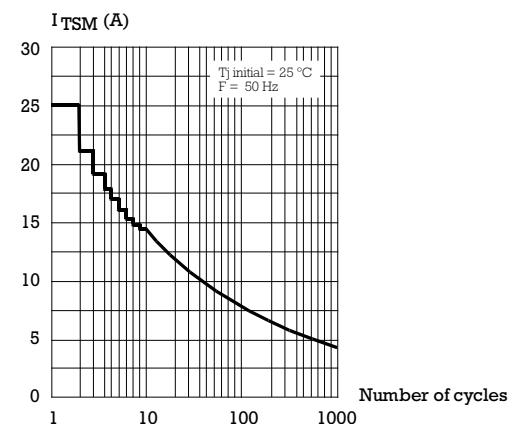


Fig. 6: Non repetitive surge peak on-state current versus number of cycles.



SURFACE MOUNT TRIAC

Fig. 7: Non repetitive surge peak on-state current for a sinusoidal pulse with width: $t_p = 10$ ms, and corresponding value of I^2t .

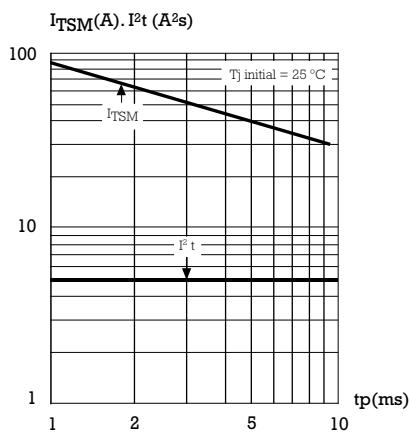


Fig. 8: On-state characteristics (maximum values).

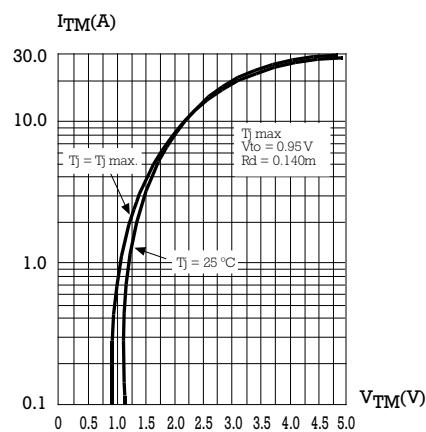
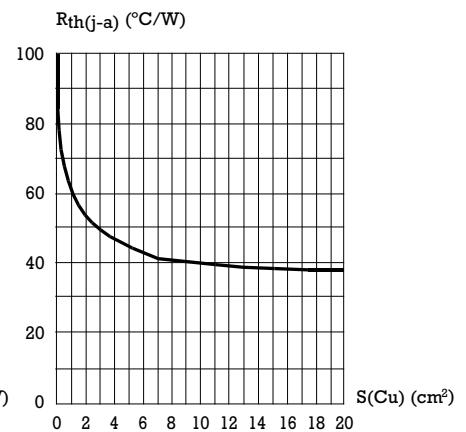


Fig. 9: Thermal resistance junction to ambient versus copper surface under tab (Epoxy printed circuit board FR4, copper thickness: 35 μm).



SURFACE MOUNT TRIAC

PACKAGE MECHANICAL DATA DPAK TO 252-AA

REF.	DIMENSIONS		
	Milimeters		
	Min.	Nominal	Max.
A	2.18	2.3±0.18	2.39
A1	0	0.12	0.127
b	0.64	0.75±0.1	0.89
c	0.46		0.61
c1	0.46		0.56
c2		0.8±0.013	
D	5.97	6.1±0.1	6.22
D1	5.21		5.52
E	6.35	6.58±0.14	6.73
E1	5.20	5.36±0.1	5.46
e		2.28BSC	
H	9.40	9.90±0.15	10.41
L	1.40		1.78
L1	2.55	2.6±0.05	2.74
L2	0.46	0.5±0.013	0.58
L3	0.89	1.20±0.05	1.27
L4	0.64	0.83±0.1	1.02

Marking: type number

Weight: 0.2 g

FOOT PRINT

